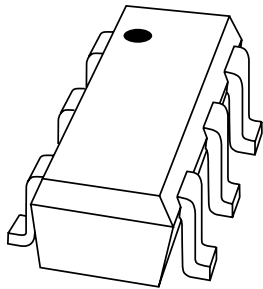


# DATA SHEET



## **BC847BPN** NPN/PNP general purpose transistor

Product specification  
Supersedes data of 1999 Apr 26

2001 Oct 26

# NPN/PNP general purpose transistor

# BC847BPN

### FEATURES

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and boardspace
- No mutual interference between the transistors.

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

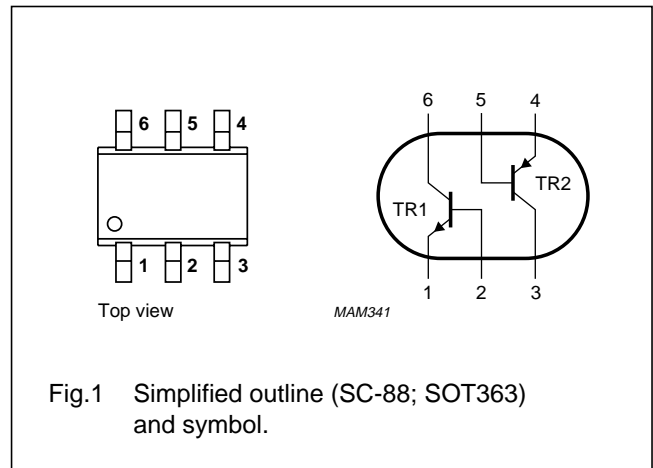
NPN/PNP transistor pair in an SC-88; SOT363 plastic package.

### MARKING

TYPE NUMBER	MARKING CODE
BC847BPN	13t

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	45	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	200	mA
$I_{BM}$	peak base current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	200	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		–65	+150	$^\circ\text{C}$
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	–	300	mW

### Note

1. Device mounted on an FR4 printed-circuit board.

## NPN/PNP general purpose transistor

BC847BPN

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
<b>Per device</b>				
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

**Note**

1. Device mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

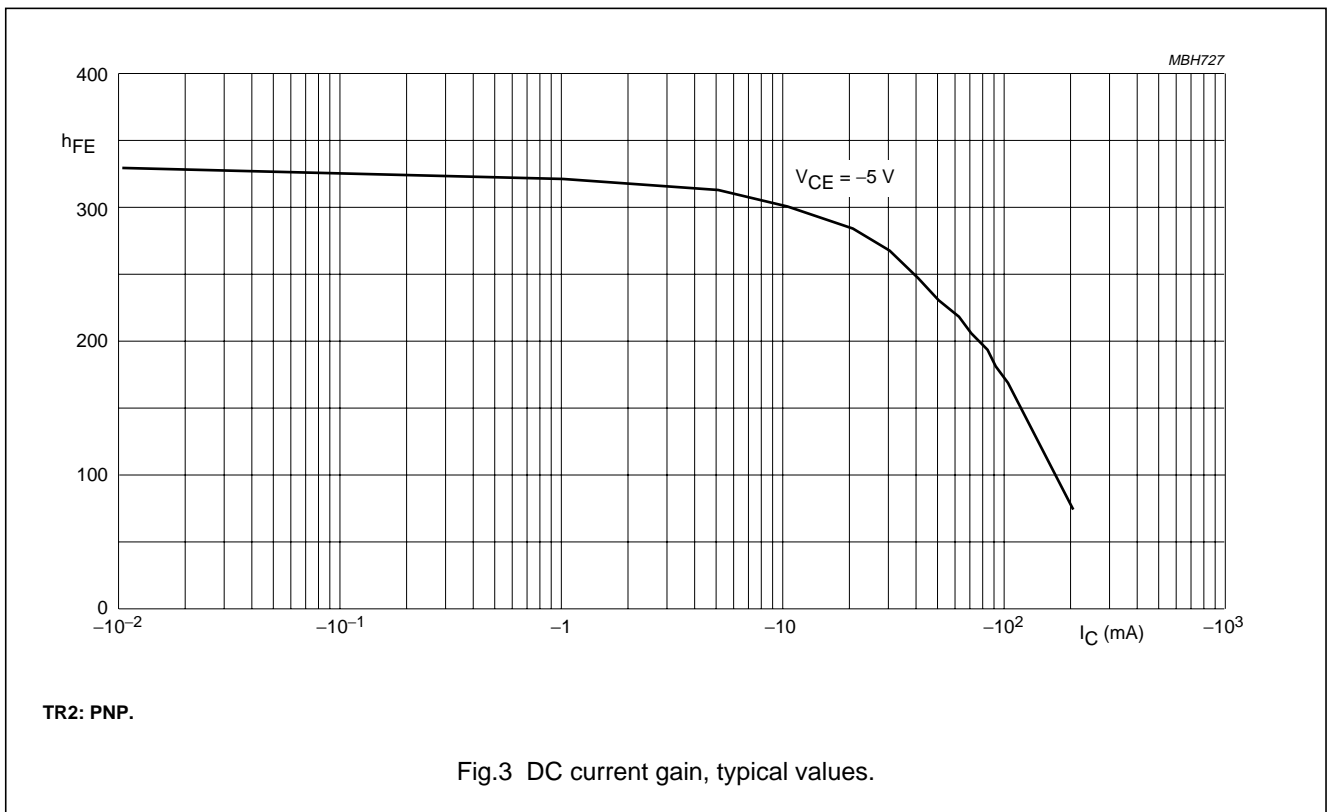
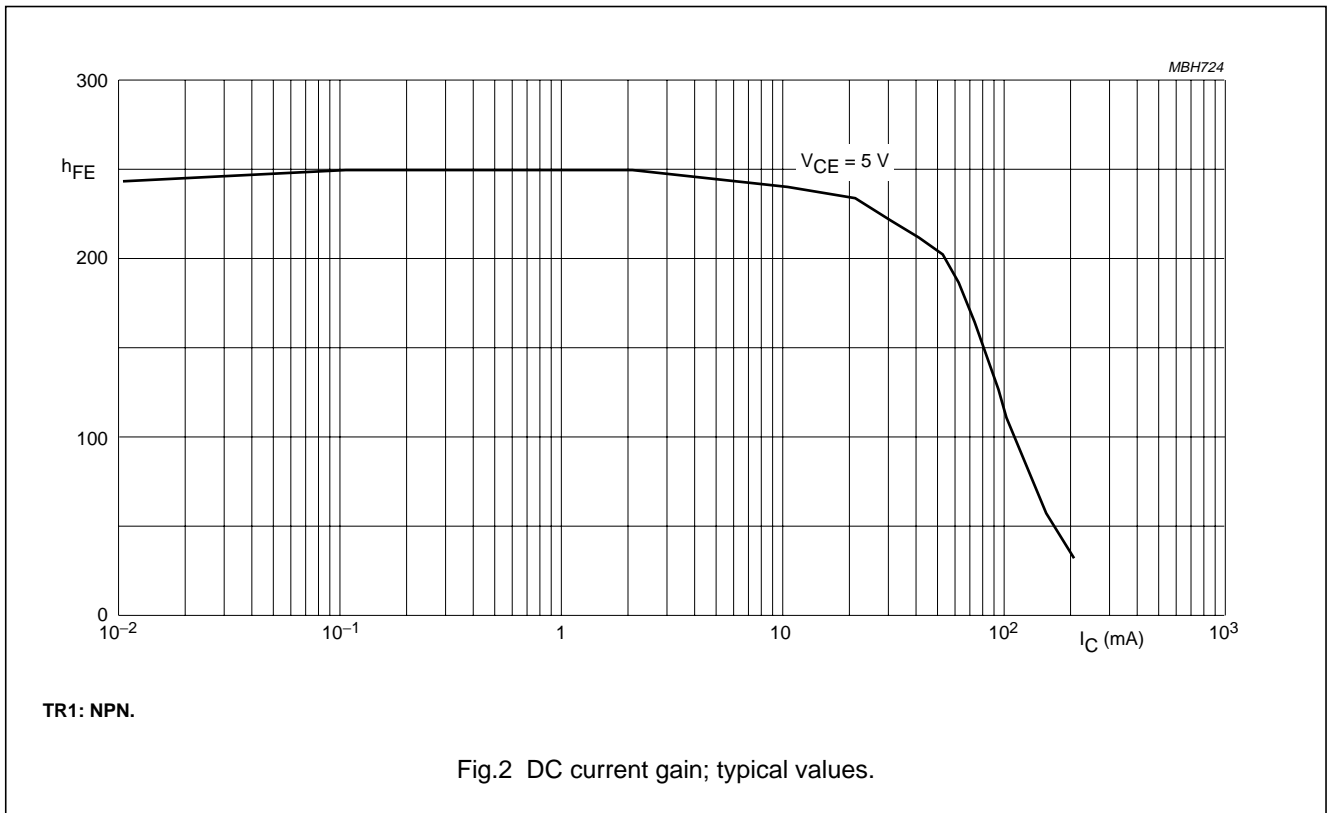
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	200	–	450	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	100	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	–	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	755	–	mV
$V_{BE}$	base-emitter voltage TR1 NPN TR2 PNP	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	580	655	700	mV
			600	655	750	mV
$C_c$	collector capacitance TR1 NPN TR2 PNP	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	1.5	pF
			–	–	2.2	pF
$C_e$	emitter capacitance TR1 NPN TR2 PNP	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	11	–	pF
			–	10	–	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

NPN/PNP general purpose transistor

BC847BPN



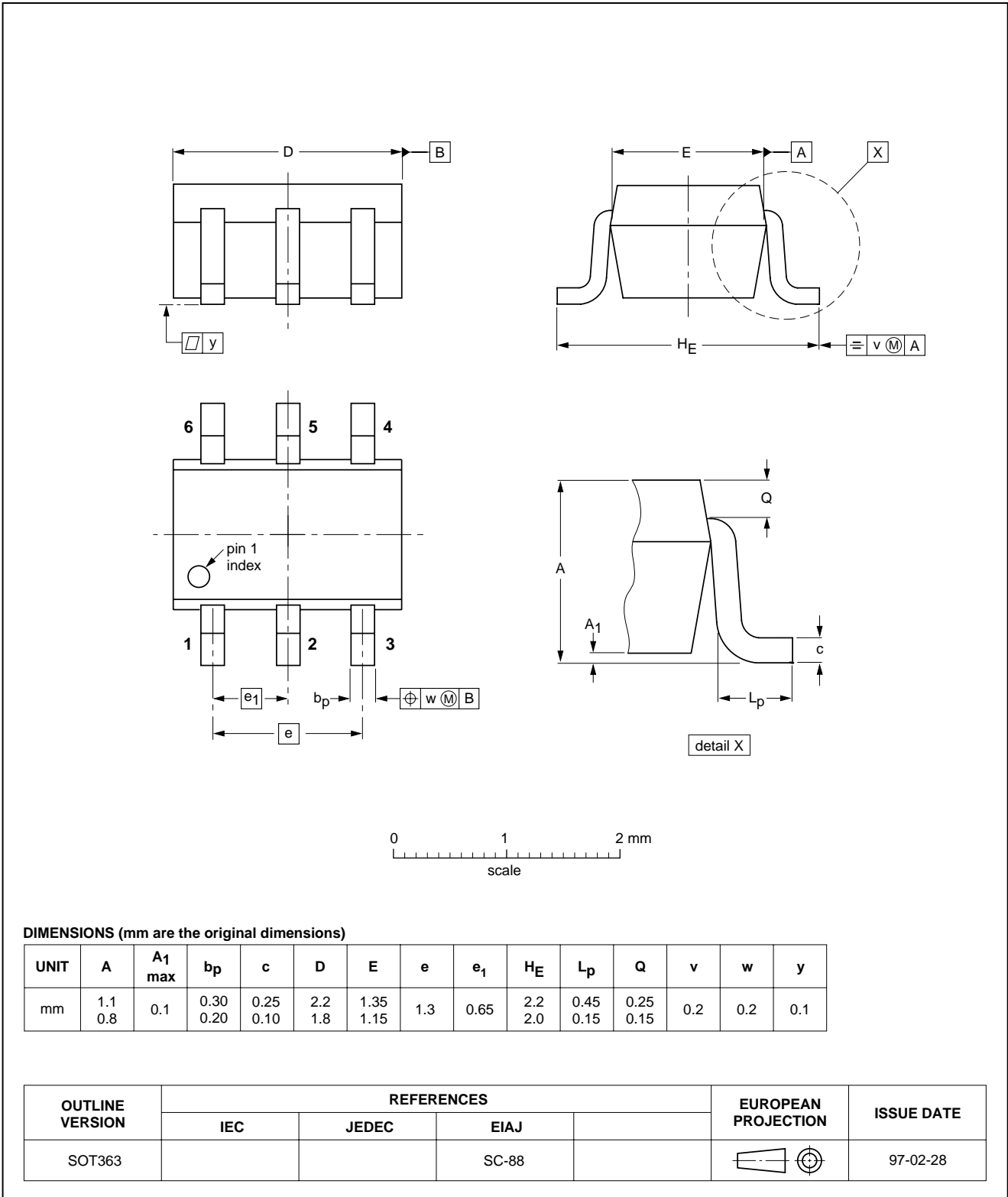
NPN/PNP general purpose transistor

BC847BPN

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



## NPN/PNP general purpose transistor

BC847BPN

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NPN/PNP general purpose transistor

BC847BPN

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**NOTES**

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## **Contact information**

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com).

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